BTA312B-600CT

3Q Hi-Com Triac

4 October 2012

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series CT" triac will commutate the full RMS current at maximum rated junction temperature ($T_j = 150~{\rm ^{\circ}C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High junction operating temperature capability
- High voltage capability
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	100	А
Tj	junction temperature		-	-	150	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 125$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	12	А





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	I _{GT} gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	-	35	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		sym051
3	G	gate		J
mb	T2	mounting base; main terminal 2	1 3	
			D2PAK (SOT404)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA312B-600CT	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 125$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	100	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	110	А

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Symbol	Parameter	Conditions	Min	Max	Unit
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	50	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

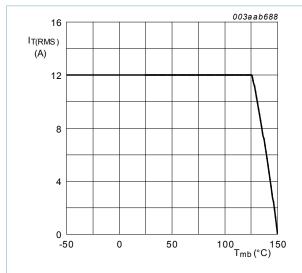
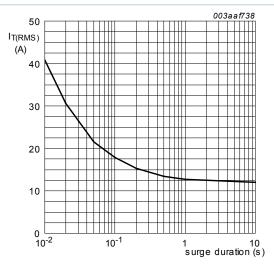


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 125 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

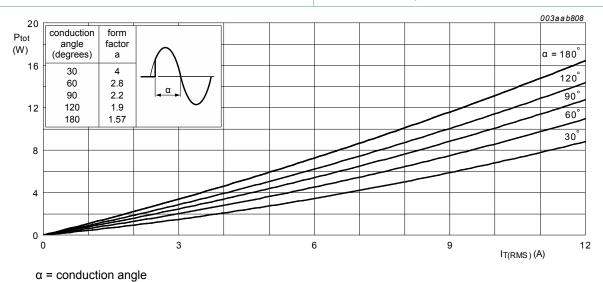


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

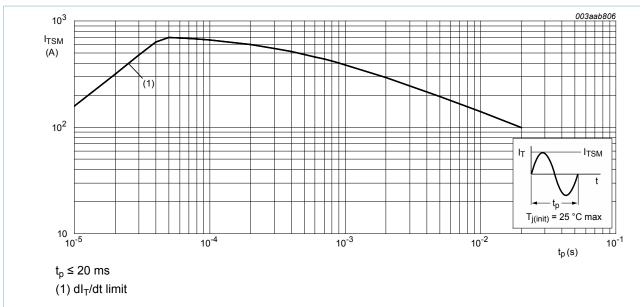


Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values

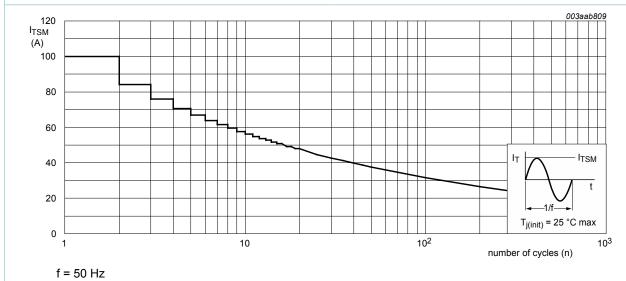


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

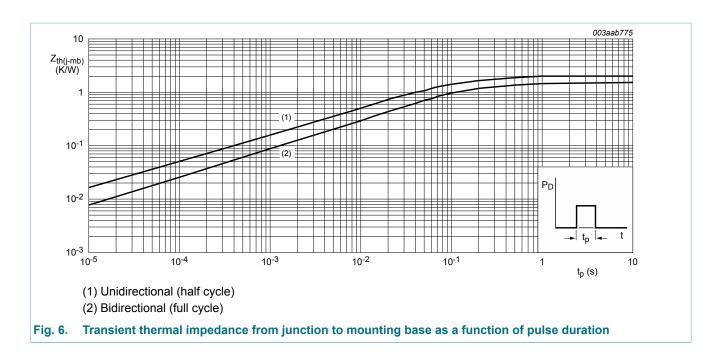
5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1.5	K/W
		half cycle; Fig. 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted; minimum footprint	-	55	-	K/W

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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	-	35	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	35	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ Fig. 10	0.25	-	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.4	2	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	13	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 1 V/ μ s; gate open circuit	20	-	-	A/ms

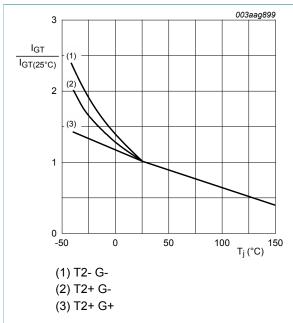


Fig. 7. Normalized gate trigger current as a function of junction temperature

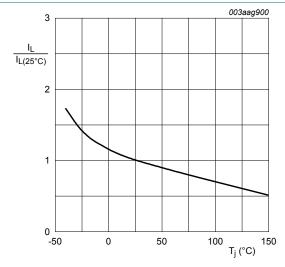
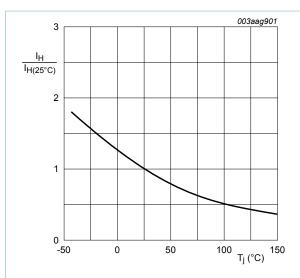


Fig. 8. Normalized latching current as a function of junction temperature



0.8

0.4

-50

0 50

1.0

003aag902

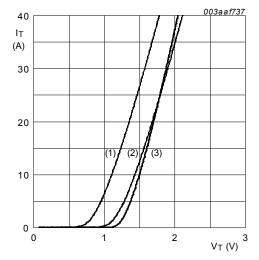
0.4

0.7

150

Fig. 9. Normalized holding current as a function of junction temperature

Fig. 10. Normalized gate trigger voltage as a function of junction temperature



Vo = 1.127 V; Rs = 0.027 Ω

(1) Tj = 150 °C; typical values

(2) Tj = 150 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

7. Package outline

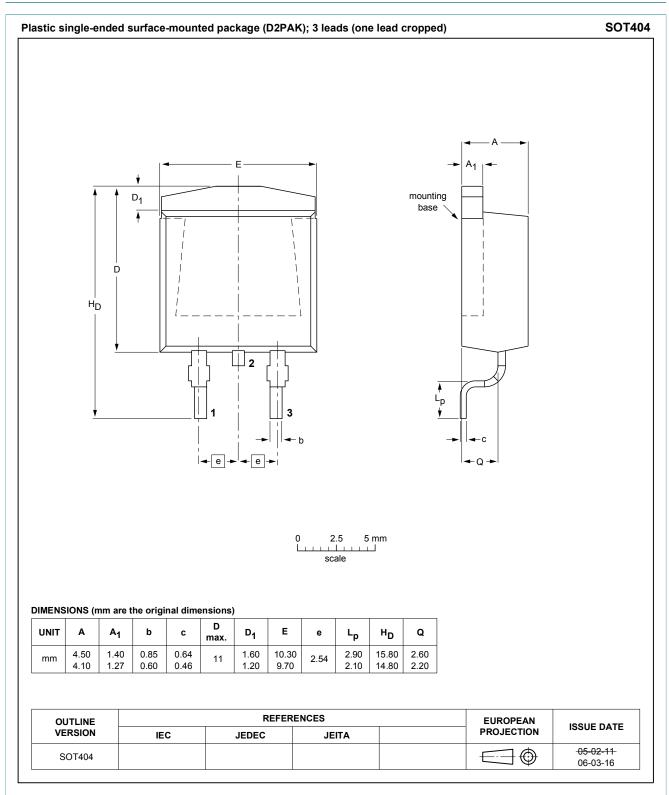
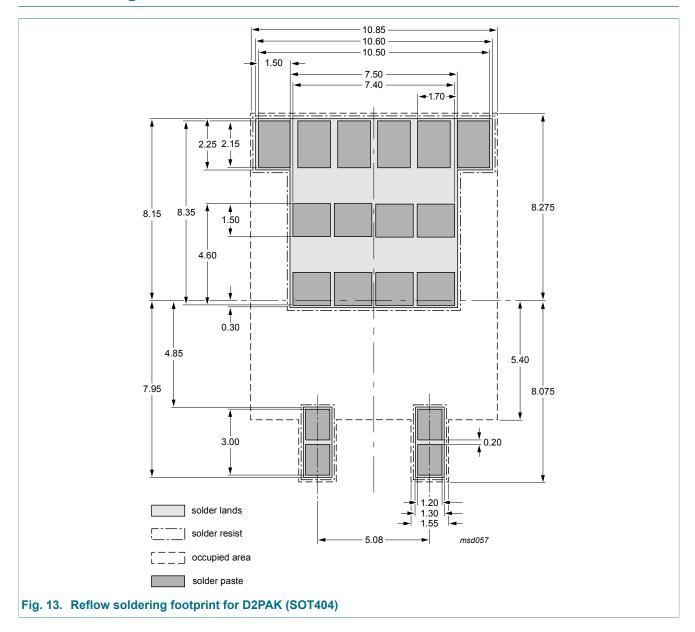


Fig. 12. Package outline D2PAK (SOT404)

8. Soldering



9. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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